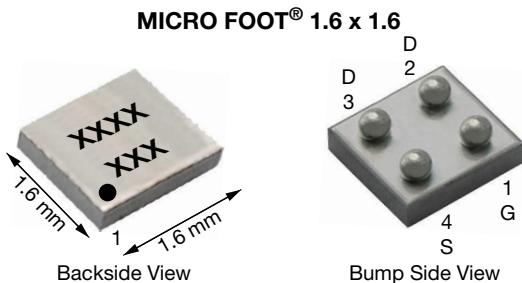


P-Channel 20 V (D-S) MOSFET



FEATURES

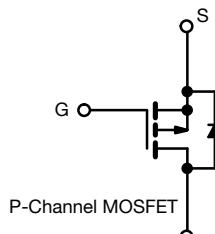
- TrenchFET® Gen III p-channel power MOSFET
- Low 0.6 mm maximum height
- Low on-resistance
- Material categorization:
for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load switch
 - With low voltage drop
- Power management in battery-operated, mobile, and wearable devices



PRODUCT SUMMARY

V _{DS} (V)	-20
R _{DS(on)} max. (Ω) at V _{GS} = -4.5 V	0.021
R _{DS(on)} max. (Ω) at V _{GS} = -2.5 V	0.025
R _{DS(on)} max. (Ω) at V _{GS} = -1.8 V	0.039
Q _g typ. (nC)	31.2
I _D (A)	-9.7 ^a
Configuration	Single

ORDERING INFORMATION

Package	MICRO FOOT
Lead (Pb)-free and halogen-free	Si8481DB-T1-E1

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DS}	-20	V	
Gate-source voltage	V _{GS}	± 8		
Continuous drain current (T _J = 150 °C)	I _D	-9.7 ^a	A	
		-7.8 ^a		
		-6.2 ^b		
		-5 ^b		
Pulsed drain current (t = 100 μs)	I _{DM}	-30	A	
Continuous source-drain diode current	I _S	-2.3 ^a		
		-0.92 ^b		
Maximum power dissipation	P _D	2.8 ^a	W	
		1.8 ^a		
		1.1 ^b		
		0.73 ^b		
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +150	°C	
Package reflow conditions ^c	VPR	260		
	IR / convection			

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^{a, f}	R _{thJA}	35	45	°C/W
Maximum junction-to-ambient ^{b, g}		85	110	

Notes

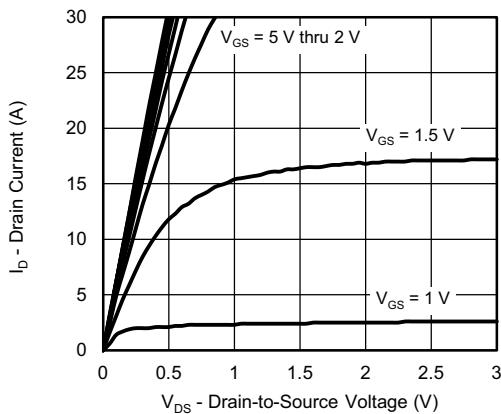
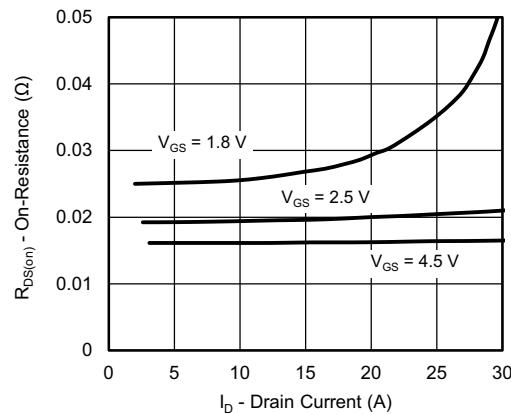
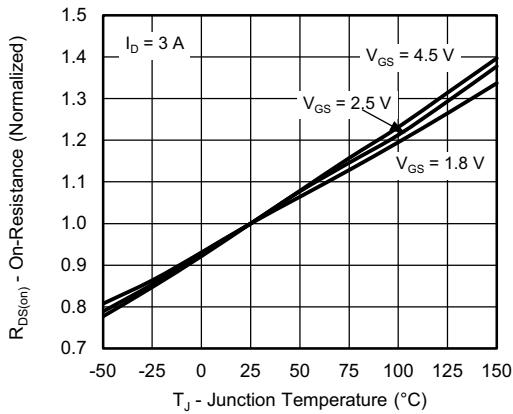
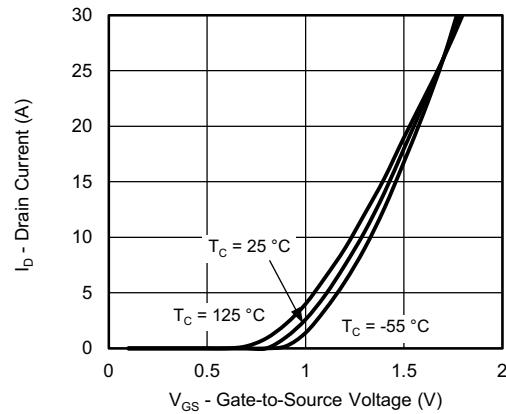
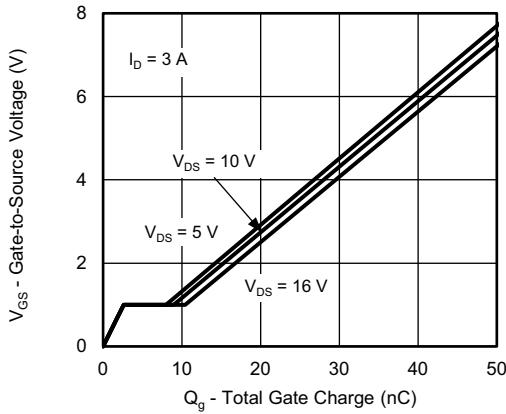
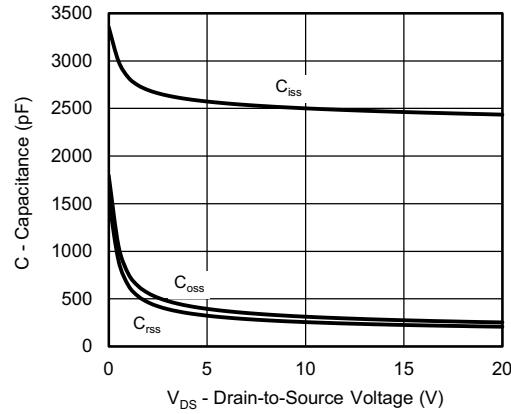
- Surface mounted on 1" x 1" FR4 board with full copper, t = 5 s.
- Surface mounted on 1" x 1" FR4 board with minimum copper, t = 5 s.
- Refer to IPC / JEDEC® (J-STD-020), no manual or hand soldering.
- In this document, any reference to case represents the body of the MICRO FOOT device and foot is the bump.
- Based on T_A = 25 °C.
- Maximum under steady state conditions is 85 °C/W.
- Maximum under steady state conditions is 175 °C/W.

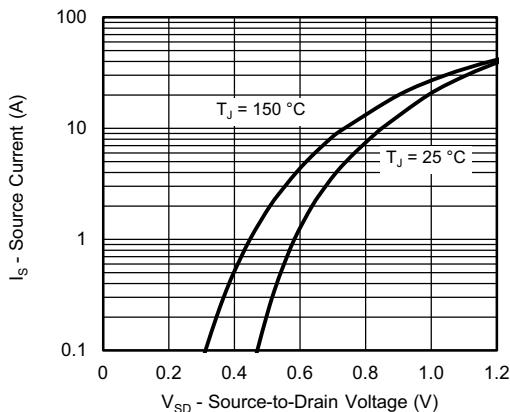
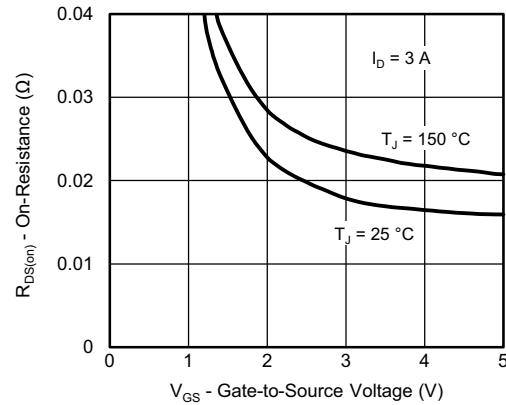
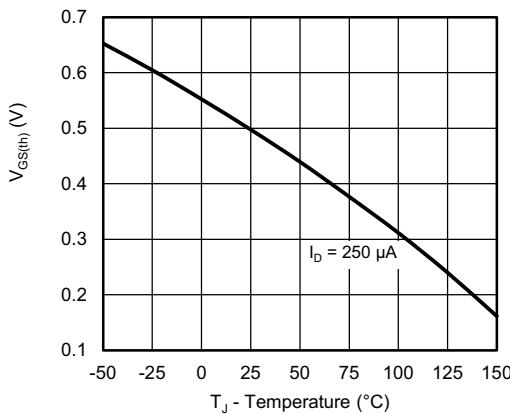
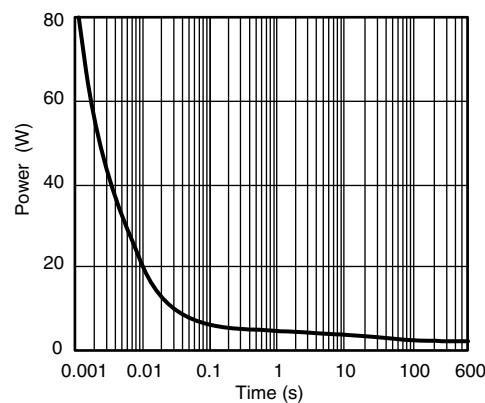
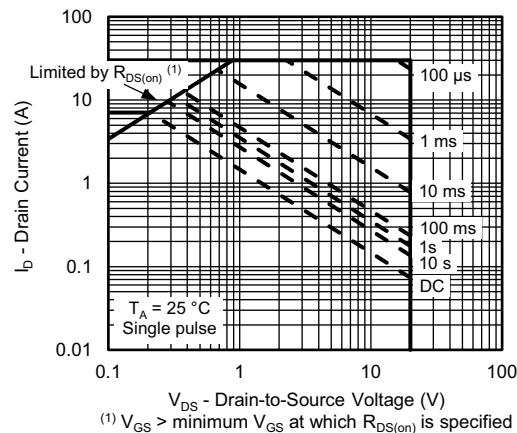
SPECIFICATIONS ($T_J = 25^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}$, $I_D = -250 \mu\text{A}$	-20	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = -250 \mu\text{A}$	-	-13	-	$\text{mV}/^\circ\text{C}$
$V_{GS(\text{th})}$ temperature coefficient	$\Delta V_{GS(\text{th})}/T_J$		-	2.5	-	
Gate-source threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	-0.4	-	-0.9	V
Gate-source leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 8 \text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20 \text{ V}$, $V_{GS} = 0 \text{ V}$	-	-	-1	μA
		$V_{DS} = -20 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 55^\circ\text{C}$	-	-	-10	
On-state drain current ^a	$I_{D(\text{on})}$	$V_{DS} \leq -5 \text{ V}$, $V_{GS} = -4.5 \text{ V}$	-5	-	-	A
Drain-source on-state resistance ^a	$R_{DS(\text{on})}$	$V_{GS} = -4.5 \text{ V}$, $I_D = -3 \text{ A}$	-	0.017	0.021	Ω
		$V_{GS} = -2.5 \text{ V}$, $I_D = -3 \text{ A}$	-	0.020	0.025	
		$V_{GS} = -1.8 \text{ V}$, $I_D = -1 \text{ A}$	-	0.026	0.039	
Forward transconductance ^a	g_{fs}	$V_{DS} = -5 \text{ V}$, $I_D = -3 \text{ A}$	-	22	-	S
Dynamic ^b						
Input capacitance	C_{iss}	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	-	2500	-	pF
Output capacitance	C_{oss}		-	320	-	
Reverse transfer capacitance	C_{rss}		-	260	-	
Total gate charge	Q_g	$V_{DS} = -10 \text{ V}$, $V_{GS} = -8 \text{ V}$, $I_D = -3 \text{ A}$	-	54	81	nC
		$V_{DS} = -10 \text{ V}$, $V_{GS} = -4.5 \text{ V}$, $I_D = -3 \text{ A}$	-	31.2	47	
Gate-source charge	Q_{gs}	$V_{DS} = -10 \text{ V}$, $V_{GS} = -4.5 \text{ V}$, $I_D = -3 \text{ A}$	-	2.7	-	nC
Gate-drain charge	Q_{gd}		-	6.3	-	
Gate resistance	R_g	$f = 1 \text{ MHz}$	-	17	-	Ω
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD} = -10 \text{ V}$, $R_L = 3.3 \Omega$, $I_D \geq -3 \text{ A}$, $V_{GEN} = -4.5 \text{ V}$, $R_g = 1 \Omega$	-	16	30	ns
Rise time	t_r		-	25	50	
Turn-off delay time	$t_{d(\text{off})}$		-	300	600	
Fall time	t_f		-	110	220	
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD} = -10 \text{ V}$, $R_L = 3.3 \Omega$, $I_D \geq -3 \text{ A}$, $V_{GEN} = -8 \text{ V}$, $R_g = 1 \Omega$	-	7	15	ns
Rise time	t_r		-	20	40	
Turn-off delay time	$t_{d(\text{off})}$		-	400	800	
Fall time	t_f		-	110	220	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	$T_A = 25^\circ\text{C}$	-	-	-2.3 $^\circ\text{C}$	A
Pulse diode forward current	I_{SM}		-	-	-15	
Body diode voltage	V_{SD}	$I_S = -3 \text{ A}$, $V_{GS} = 0 \text{ V}$	-	-0.8	-1.2	V
Body diode reverse recovery time	t_{rr}	$I_F = -3 \text{ A}$, $di/dt = 100 \text{ A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$	-	150	300	ns
Body diode reverse recovery charge	Q_{rr}		-	235	470	nC
Reverse recovery fall time	t_a		-	47	-	
Reverse recovery rise time	t_b		-	103	-	ns

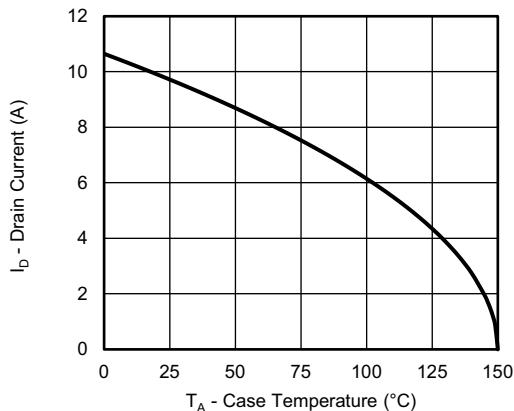
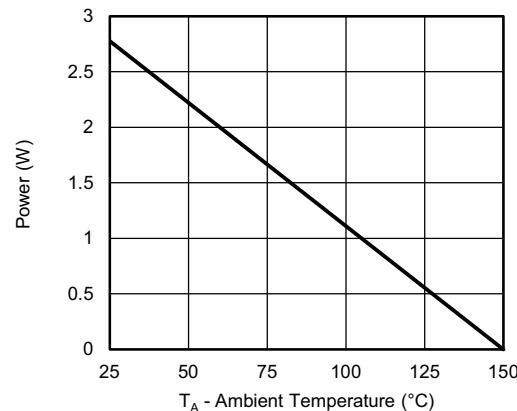
Notes

- Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Surface mounted on 1" x 1" FR4 board with full copper, $t = 5 \text{ s}$.

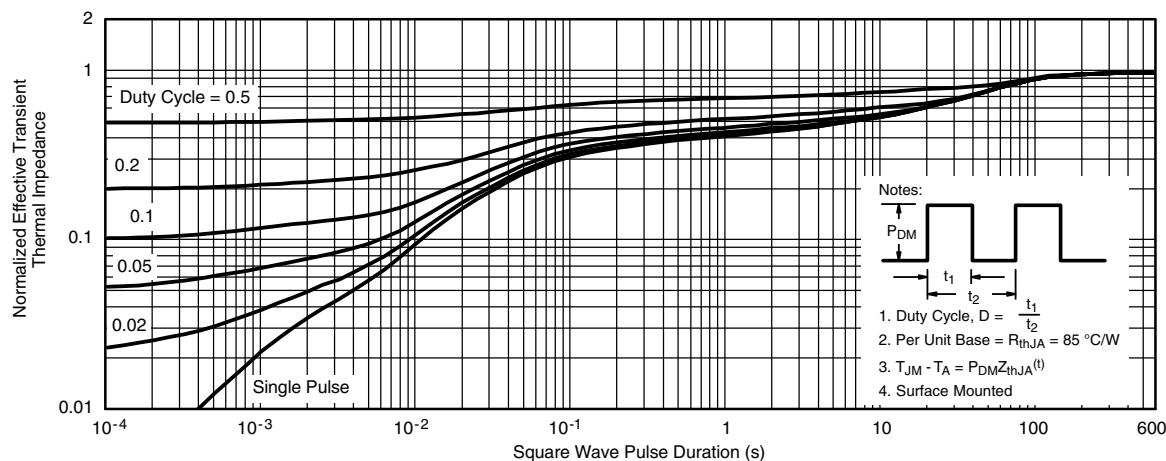
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

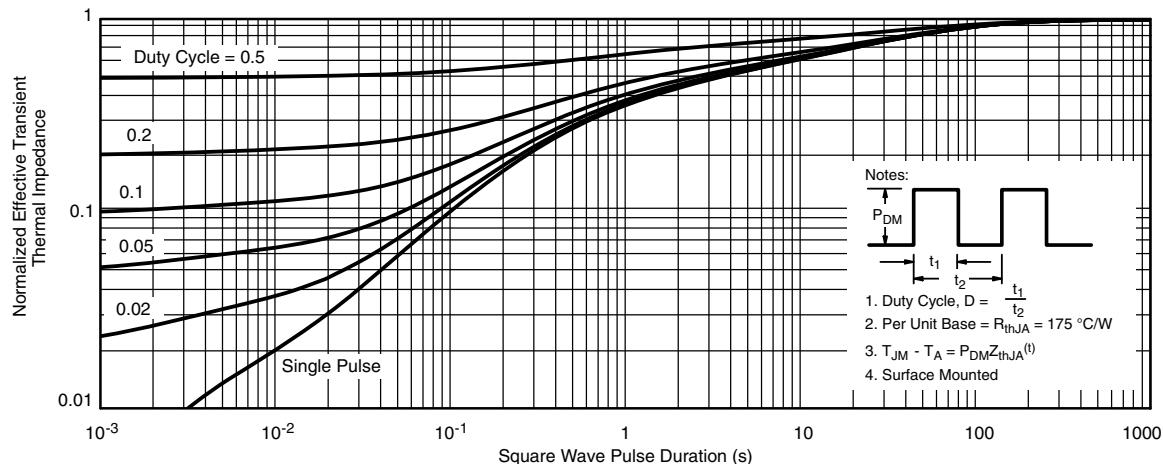
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

On-Resistance vs. Drain Current and Gate Voltage

On-Resistance vs. Junction Temperature

Transfer Characteristics

Gate Charge

Capacitance

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power, Junction-to-Ambient

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating ^a

Power, Junction-to-Ambient ^a
Note

a. When surface mounted on 1" x 1" FR4 board with full copper, $t = 5$ s.


Normalized Thermal Transient Impedance, Junction-to-Ambient (on 1" x 1" FR4 board with maximum copper)

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


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